ABSOLUTE MAXIMUM RATINGS

ADJ, IN, BIAS, PGOOD, SHDN, OUT to GND0.3V to +6V
Output Short-Circuit Duration
Continuous Power Dissipation ($T_A = +70$ °C)
6-Pin SOT23 (derate 8.7mW/°C above +70°C)696mW
Operating Temperature Range40°C to +85°C

Junction Temperature	+150°C
	65°C to +150°C
	10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 3, $V_{IN} = 1.8V$, $I_{LOAD} = 1$ mA, $C_{LOAD} = 10\mu$ F, $T_A = 0$ °C to +85°C, unless otherwise noted. Typical values are at $T_A = +25$ °C.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Input Voltage	V _{IN}		1.25		5.5	V	
BIAS Voltage	V _{BIAS}		4.5		5.5	V	
V _{OUT} Voltage Range	Vout	MAX1983	0.8		2.0	V	
BIAS Input Undervoltage Lockout			3.8	4.1	4.35	V	
Shutdown Supply Current	I _{IN}	1.25V < V _{IN} < 5.5V		1	5	μΑ	
Quiescent BIAS Current	IQ	4.5V < V _{BIAS} < 5.5V		140	250	μΑ	
Shutdown BIAS Current	ISHDN	4.5V < V _{BIAS} < 5.5V		1	5	μΑ	
Vous Input Dies Current		MAX1982: V _{IN} = open, V _{OUT} = 1.20V			30		
V _{OUT} Input Bias Current		MAX1983: V _{IN} = open, 0.8V < V _{OUT} < 2.0V			2	μΑ	
MAX1983 ADJ Input Current		0V < V _{ADJ} < 2.0V			1	μΑ	
REGULATOR CHARACTERISTIC	S						
Line Regulation	$\Delta V_{ ext{OUT}}/$ $\Delta V_{ ext{IN}}$	I _{LOAD} = 10mA, 1.5V < V _{IN} < 5.5V	-0.15		+0.15	%/V	
		$T_A = +25^{\circ}C$, $I_{OUT} = 100mA$	-1		+1	%	
MAX1982 1.20V Output Voltage Accuracy	Vout	$T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}, \ I_{OUT} = 1\text{mA to } 300\text{mA}, \ V_{OUT} + 0.5\text{V} < V_{IN} < 5.5\text{V}$	-3		+3		
		$T_A = +25^{\circ}C$, $I_{OUT} = 100mA$	-1		+1		
MAX1983 0.80V Output Voltage Accuracy	Vout	$T_A = 0^{\circ}\text{C to } +85^{\circ}\text{C}, \ I_{OUT} = 1\text{mA to } 300\text{mA}, \ V_{OUT} + 0.5\text{V} < V_{IN} < 5.5\text{V}$	-3		+3	%	
Duna a si Malta a s		I _{LOAD} = 300mA			350	>/	
Dropout Voltage	V _{DO}	I _{LOAD} = 150mA			175	mV	
Current Limit	I _{LIM}	V _{IN} - V _{OUT} = 1.3V	330	600	1400	mA	
Thermal-Shutdown Temperature	TSHDN			160		°C	
Thermal-Shutdown Hysteresis				20		°C	
RMS Output Noise		10Hz to 100kHz		65		μV _{RMS}	
PGOOD COMPARATOR							
Comparator Threshold		% of regulated output voltage	-12.5	-9	-6	%	
Comparator Hysteresis	V _H YST			10		mV	

__ /N/XI/N

ELECTRICAL CHARACTERISTICS (continued)

(Circuit of Figure 3, V_{IN} = 1.8V, I_{LOAD} = 1mA, C_{LOAD} = 10 μ F, T_A = 0°C to +85°C, unless otherwise noted. Typical values are at T_A = +25°C.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
LOGIC AND I/O			-			
SHDN Input High Voltage	VIH		2.4			V
SHDN Input Low Voltage	VIL				0.8	V
SHDN Input Current			-1		+1	μΑ
PGOOD Output Low Voltage		PGOOD sinking 1mA			0.1	V
PGOOD Output High Leakage Current		0 < V _{PGOOD} < V _{IN}	-1		+1	μА
DYNAMICS						
Positive Load Step	trise	$I_{LOAD} = 1 \text{mA}$ to full load, $C_{LOAD} = 10 \mu\text{F}$		10		μs
Negative Load Step	tfall	I _{LOAD} = full load to 1mA, C _{LOAD} = 10μF		50		μs
Ripple Rejection at V _{IN}		$10Hz < f < 10kHz$, $I_{LOAD} = 300mA$, $C_{LOAD} = 10\mu F$		-60		dB
Startup Response Time	ton	I _{LOAD} = 300mA, C _{LOAD} = 10μF, 0% to 90% of nominal output voltage		100		μs
Startup Overshoot		$I_{LOAD} = 300$ mA, $C_{LOAD} = 10$ μ F		0.5		%
DCOOD Propagation Dalay	too	Falling edge, 3mV under trip threshold		10		μs
PGOOD Propagation Delay	t _{PD}	Rising edge within 5% of regulation level	1	•	4	ms

ELECTRICAL CHARACTERISTICS

(Circuit of Figure 3, V_{IN} = 1.8V, I_{LOAD} = 1mA, C_{LOAD} = 10µF, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS		
Input Voltage	V _{IN}		1.25	5.5	V		
BIAS Voltage	V _{BIAS}		4.5	5.5	V		
V _{OUT} Voltage Range	Vout	MAX1983	0.8	2.0	٧		
BIAS Input Undervoltage Lockout			3.8	4.2	٧		
Shutdown Supply Current	I _{IN}	1.25V < V _{IN} < 5.5V		5	μΑ		
Quiescent BIAS Current	IQ	4.5V < V _{BIAS} < 5.5V		250	μΑ		
Shutdown BIAS Current	ISHDN	4.5V < V _{BIAS} < 5.5V		5	μΑ		
Vol. = Input Bigs Current		MAX1982: V _{IN} = open, V _{OUT} = 1.20V		30	^		
VOUT Input Bias Current		MAX1983: V _{IN} = open, 0.8V < V _{OUT} < 2.0V		2	μA		
REGULATOR CHARACTERISTIC	REGULATOR CHARACTERISTICS						
Line Regulation	$\Delta V_{ ext{OUT}} / \Delta V_{ ext{IN}}$	I _{LOAD} = 10mA, 1.5V < V _{IN} < 5.5V	-0.15	+0.15	%/V		
MAX1982 1.20V Output Voltage Accuracy	V _{OUT}	$I_{OUT} = 1$ mA to 300mA, $V_{OUT} + 0.5$ V < $V_{IN} < 5.5$ V	-3	+3	%		

ELECTRICAL CHARACTERISTICS (continued)

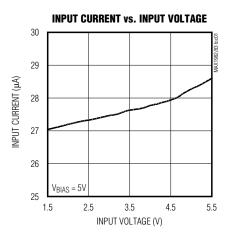
(Circuit of Figure 3, V_{IN} = 1.8V, V_{OUT} = 1.2V, I_{LOAD} = 1mA, C_{LOAD} = 10µF, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 1)

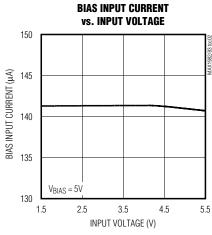
PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNITS	
MAX1983 0.80V Output Voltage Accuracy	V _{OUT}	I _{OUT} = 1mA to 300mA, V _{OUT} + 0.5V < V _{IN} < 5.5V	-3	+3	%	
Drangut Valtage		$I_{LOAD} = 300 mA$		350	.,	
Dropout Voltage	V _{DO}	I _{LOAD} = 150mA		175	mV	
Current Limit	I _{LIM}	V _{IN} - V _{OUT} = 1.3V	330	1400	mA	
PGOOD COMPARATOR						
Comparator Threshold		% of regulated output voltage	-12.5	-6	%	
LOGIC AND I/O						
SHDN Input High Voltage	VIH		2.4		V	
SHDN Input Low Voltage	VIL			0.8	V	
SHDN Input Current			-1	+1	μΑ	
PGOOD Output Low Voltage		PGOOD sinking 1mA		0.1	V	
PGOOD Output High Leakage Current		0 < VPGOOD < VIN	-1	+1	μΑ	
DYNAMICS						
PGOOD Propagation Delay	tpD	Rising edge within 5% of regulation level	1	4	ms	

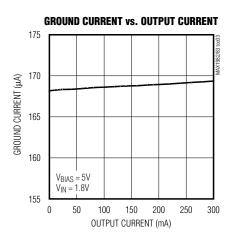
Note 1: Specifications over temperature are guaranteed by design, not production tested. **Note 2:** V_{OUT} is 1.2V for MAX1982. For MAX1983 V_{OUT} is set to 1.2V with circuit of Figure 4.

Typical Operating Characteristics

(Circuit of Figure 3, $T_A = +25$ °C, unless otherwise noted.)



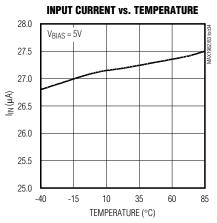


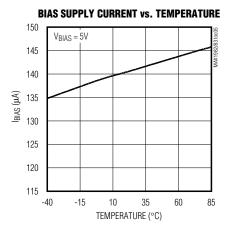


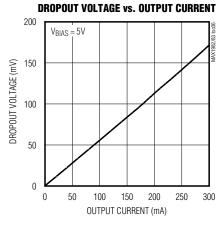
4 ______ *NIXIN*

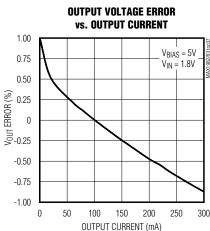
Typical Operating Characteristics (continued)

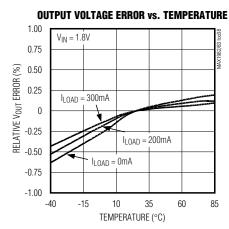
(Circuit of Figure 3, $T_A = +25$ °C, unless otherwise noted.)

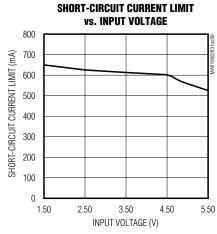


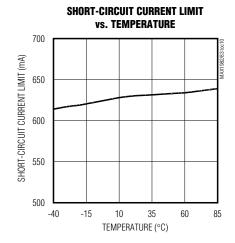


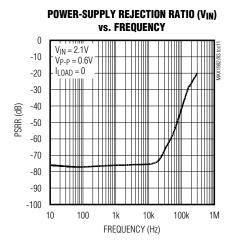








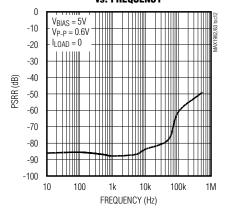


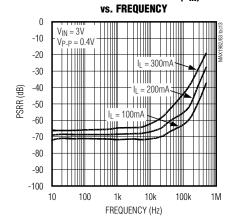


Typical Operating Characteristics (continued)

(Circuit of Figure 3, $T_A = +25$ °C, unless otherwise noted.)

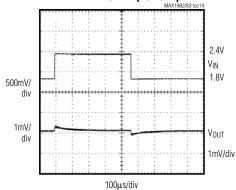




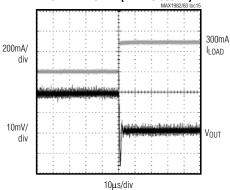


RIPPLE REJECTION RATIO (VIN)

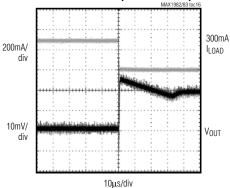
LINE TRANSIENT (NO LOAD)



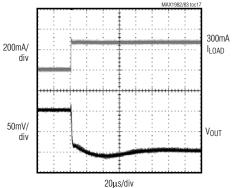
LOAD TRANSIENT (1mA TO 300mA)



LOAD TRANSIENT (300mA TO 1mA)

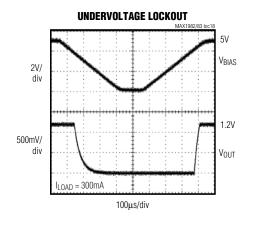


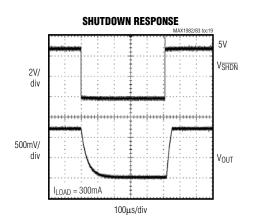
LOAD TRANSIENT IN DROPOUT

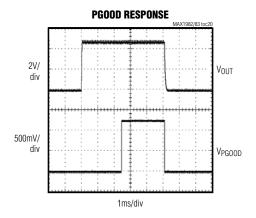


Typical Operating Characteristics (continued)

(Circuit of Figure 3, $T_A = +25$ °C, unless otherwise noted.)







Pin Description

PIN		NABAE	FUNCTION		
MAX1982	MAX1983	NAME	FUNCTION		
1	1	BIAS	Bias Voltage. Input voltage to the control circuitry. BIAS powers all control blocks and the gate of the pass transistor. Bypass BIAS to GND with a 0.1µF ceramic capacitor.		
2	2	GND	Ground		
3	3	SHDN	Shutdown Control Input. Drive SHDN low to enter the low-power shutdown state. Connect SHDN to BIAS for normal operation.		
4		PGOOD	Power-Good Output. The open-drain PGOOD output goes high at least 1ms after the output voltage has attained regulation. PGOOD asserts low 10µs after the output falls by 10%.		
_	4	ADJ	Feedback for Adjustable Output. Connect ADJ to the midpoint of a resistor-divider between OUT and GND for an adjustable output voltage between 0.8V and 2.0V.		
5	5	OUT	Regulator Output. Bypass OUT to GND with a 10µF to 22µF low-ESR ceramic capacitor.		
6	6	IN	Internal Pass Transistor Input. IN connects to the drain of the internal power switch. Bypass IN to GND with a 10µF ceramic capacitor.		

Detailed Description

The MAX1982/MAX1983 are low-voltage, low-dropout linear regulators with an external bias supply input (see Figures 1 and 2). BIAS is powered by a 4.5V to 5.5V supply that is commonly available in laptop and desk-top computers. The 5V bias supply drives the gate of the internal pass transistor, while a lower voltage input at the drain of the transistor (IN) is regulated to provide Vout. Separating the bias input voltages yields higher efficiency. These devices are ideal for applications that require low-voltage outputs from low-voltage inputs. The MAX1982 delivers 1.2V (±3%) at 300mA from an input voltage of 1.25V to 5.5V. The MAX1983 delivers an adjustable output voltage from 0.8V to 2V.

The MAX1982 features an open-drain PGOOD output that transitions high 1ms after the output reaches regulation. PGOOD goes low within 10µs of the output falling out of regulation by 120mV.

Both devices feature current- and thermal-limiting circuitry that protect the MAX1982/MAX1983 from damage during fault conditions.

Bias Supply Input

The BIAS input powers the control circuitry and provides the pass transistor gate drive. Power BIAS from a well-regulated 5V (±10%) supply. Current drawn from the BIAS supply remains relatively constant with variations in V_{IN} and load current (see the *Typical Operating Characteristics*). Bypass BIAS with a 0.1µF or greater

capacitor as close to the device as possible. The bias supply current remains low ($250\mu A$) when the MAX1982/MAX1983 are in dropout.

Power-Supply Input

IN connects to the drain of the internal N-channel power transistor. IN may be as low as 1.25V, minimizing power dissipation. Bypass IN with a $10\mu F$ or greater capacitor as close to the device as possible.

Shutdown

The MAX1982/MAX1983 feature a low-power shutdown mode that reduces quiescent current drawn to $1\mu A$ (typ), and BIAS current consumption to less than $1\mu A$ (typ). Driving \overline{SHDN} low disables the voltage reference, error amplifier, gate-drive circuitry, and pass transistor (see Figure 2), and the device output enters a high-impedance state. Connect \overline{SHDN} to BIAS for normal operation.

PGOOD Output

The MAX1982 provides an open-drain PGOOD output that goes high 1ms (min) after the output attains regulation (within 10% of the nominal output voltage). PGOOD transitions low 10µs after the output falls out of regulation by 120mV, or when the device enters shutdown. Connect a pullup resistor from PGOOD to BIAS for a logic-level output. Use a $100 \mathrm{k}\Omega$ resistor to minimize current consumption.

8 /VIXI/VI

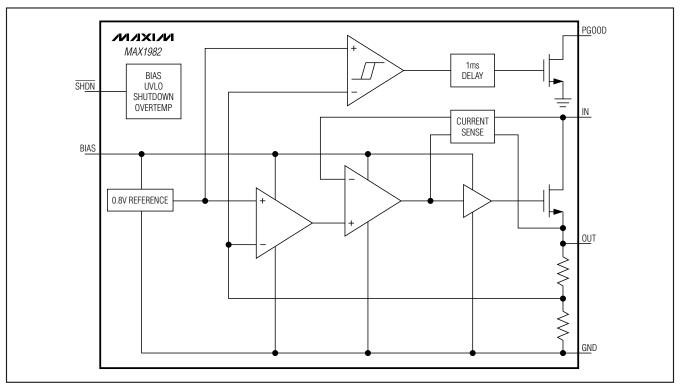


Figure 1. MAX1982 Functional Diagram

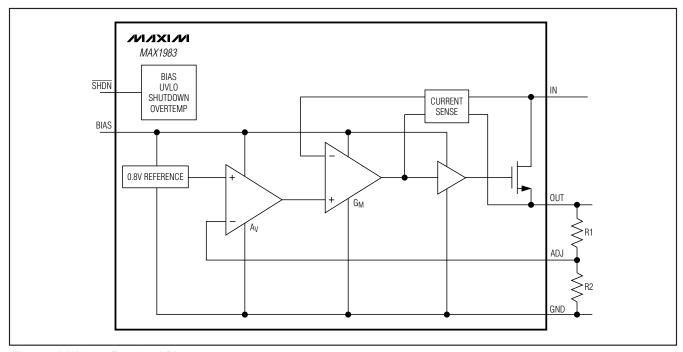


Figure 2. MAX1983 Functional Diagram

Current Limit

The MAX1982/MAX1983 limit the output current to 600mA (typ) in the event of an overload or output short circuit. The current limit prevents damage to the internal power transistor, but the device can enter thermal shutdown if the power dissipation is great enough to increase the die temperature above +160°C (see the *Thermal-Overload Protection* section).

Thermal-Overload Protection

Thermal-overload protection limits the power dissipation in the MAX1982/MAX1983. When the die temperature exceeds +160°C, the pass transistor turns off, allowing the device to cool. Normal operation resumes when the die temperature cools by 20°C. A continuous thermal-overload condition results in a pulsed output. For continuous operation, do not exceed a junction temperature of +150°C.

Applications Information

Output Voltage Selection

The MAX1982 output is fixed at 1.2V. The MAX1983 provides an adjustable output (0.8V to 2.0V). Connect ADJ to a resistive voltage-divider between OUT and

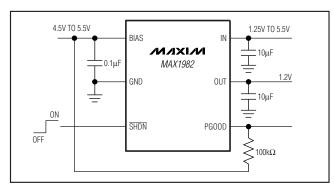


Figure 3. MAX1982 Typical Application Circuit

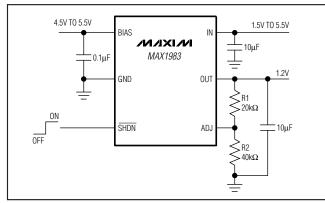


Figure 4. MAX1983 Typical Application Circuit

GND as shown in Figure 4. Set the output voltage using the following equation:

$$V_{OUT} = 0.8V \left(1 + \frac{R1}{R2} \right)$$

Set R2 at $40k\Omega$ and choose R1 to achieve the desired output voltage. Set V_{IN} to higher than (V_{OUT} + 400mV) to meet the dropout voltage requirement (see the Input/Output (Dropout) Voltage section).

To ensure stability over the specified input voltage range, the minimum output capacitance must be 10μ F with a maximum ESR of $35m\Omega$.

Operating Region and Power Dissipation

The maximum power dissipation of the MAX1982/MAX1983 depends on the thermal resistance of the 6-pin SOT23 package and the circuit board, the temperature difference between the die and ambient air, and the rate of airflow. The power dissipated in the device is:

$$P_D = I_{OUT} \times (V_{IN} - V_{OUT})$$

The resulting maximum power dissipation is:

$$P_{DISS(MAX)} = \frac{T_{J(MAX)} - T_{A}}{\theta_{JC} + \theta_{CA}}$$

where $T_{J(MAX)}$ is the maximum junction temperature (+150°C) and T_A is the ambient temperature, θ_{JC} is the thermal resistance from the die junction to the package case, and θ_{CA} is the thermal resistance from the case through the PC board, copper traces, and other materials to the surrounding air. For optimum power dissipation, use a large ground plane with good thermal contact to GND, and use wide input and output traces.

When 1 square inch of copper is connected to the device, the maximum allowable power dissipation of a 6-pin SOT23 package is 696mW. The maximum power dissipation is derated by $8.7 \text{mW}/^{\circ}\text{C}$ above $T_A = +70 ^{\circ}\text{C}$. Extra copper on the PC board increases thermal mass, and reduces thermal resistance of the board. Refer to the MAX1982/MAX1983 EV kit for a layout example.

The MAX1982/MAX1983 deliver up to 300mA and operate with input voltages up to 5.5V, but not simultaneously. High output currents can only be achieved when the input-output differential voltages are low (Figure 5).

Undervoltage Lockout (UVLO)

The undervoltage lockout (UVLO) circuit ensures that the regulator starts up with adequate voltage for the gate-drive circuitry to bias the internal pass transistor. The UVLO circuitry monitors VBIAS

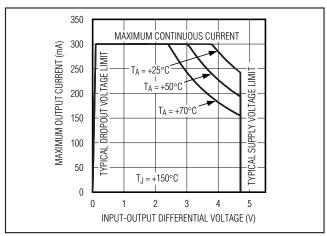


Figure 5. Power Operating Region—Maximum Output Current vs. Supply Voltage

only. The UVLO threshold is 4.2V, and V_{BIAS} must remain above this level for proper operation, regardless of the level of V_{IN} .

Input Capacitor

Bypass IN to ground with a 10µF or greater ceramic capacitor. Bypass BIAS to ground with a 0.1µF ceramic capacitor for normal operation in most applications.

Output Capacitor

Bypass OUT to ground with a low-ESR ceramic capacitor greater than 10 μ F. The ESR must be less than 35m Ω . Choose an output capacitor to maintain the required output voltage tolerance during a load step. The change in output voltage is,

$$\Delta V = I \left[ESR + \frac{\Delta t}{C_{OUT}} \right]$$

where I is the load current, C_{OUT} is the output capacitance, and Δt is the duration of the load step.

Noise, PSRR, and Transient Response

The MAX1982/MAX1983 operate with low-dropout voltage and low quiescent current in notebook computers while maintaining good noise, transient response, and AC rejection specifications. See the *Typical Operating Characteristics* for a graph of Power-Supply Rejection Ratio (PSRR) vs. Frequency. Improved supply-noise rejection and transient response can be achieved by increasing the values of the input and output capacitors and use passive filtering techniques when operating from noisy sources.

The MAX1982/MAX1983 load-transient response graphs (see the *Typical Operating Characteristics*) show two components of the output response: a DC shift from the output impedance due to the load current change and the transient response. A typical transient response for a step change in the load current from 1mA to 300mA is 20mV. Increasing the output capacitor's value and decreasing the ESR attenuate the overshoot.

Input/Output (Dropout) Voltage

A regulator's minimum input-to-output voltage differential (dropout voltage) determines the lowest usable supply voltage. In battery-powered systems, the dropout voltage determines the useful end-of-life battery voltage. Because the MAX1982/MAX1983 use an N-channel pass transistor, the dropout voltage is a function of the drain-to-source on-resistance (RDS(ON) = 1Ω max) multiplied by the load current (see the *Typical Operating Characteristics*):

 $V_{DROPOUT} = V_{IN} - V_{OUT} = R_{DS(ON)} \times I_{OUT}$

PC Board Layout Guidelines

The MAX1982/MAX1983 require proper layout to achieve the intended output power level, high efficiency, and low noise. Proper layout involves the use of a ground plane, appropriate component placement, and correct routing of traces using appropriate trace widths.

- 1) Minimize high-current ground loops. Connect the ground of the device, the input capacitor, and the output capacitor together at one point.
- 2) To optimize performance, a ground plane is essential. Use all available copper layers in applications where the device is located on a multilayer board.
- Connect the input filter capacitor less than 10mm from IN. The connecting copper trace carries large currents and must be at least 2mm wide, preferably 5mm wide.
- 4) Use as much copper as necessary to increase the thermal resistance of the device. In general, more copper provides better heatsinking capabilities.

Chip Information

_Package Information

TRANSISTOR COUNT: 430 PROCESS: BICMOS

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
6SOT23	U16-1	21-0058

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	7/02	Initial release	_
1	10/08	Added lead-free parts	1

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Maxim Integrated:

MAX1983EUT+T MAX1982EUT+T